

MOSFET

OptiMOS™ 6 Power-Transistor, 120 V

Features

- N-channel, normal level
- Very low on-resistance $R_{DS(on)}$
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low reverse recovery charge (Q_{rr})
- High avalanche energy rating
- 175°C operating temperature
- Optimized for high frequency switching
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- MSL 1 classified according to J-STD-020

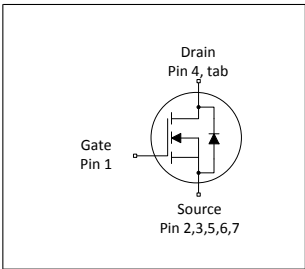
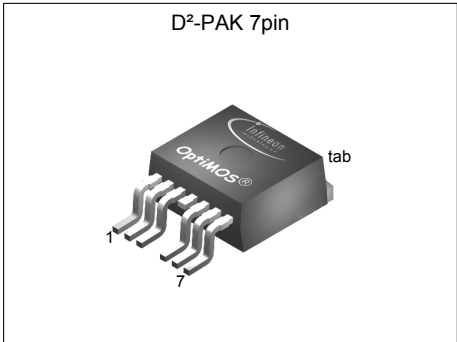
Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	120	V
$R_{DS(on),max}$	1.9	mΩ
I_D	254	A
Q_{oss}	267	nC
Q_G	113	nC
Q_{rr} (1000 A/μs)	336	nC

Type / Ordering Code	Package	Marking	Related Links
IPF019N12NM6	PG-TO263-7	019N12N6	-



RoHS

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	254 195 195 31	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=8\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}^{2)}$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	1016	A	$T_A=25\text{ °C}$
Avalanche current, single pulse ⁴⁾	I_{AS}	-	-	100	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	1406	mJ	$I_D=73\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	395 3.8	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}^{2)}$
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.38	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	40	°C/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	°C/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information.

⁴⁾ See Diagram 13 for more detailed information.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	120	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.6	3.1	3.6	V	$V_{DS}=V_{GS}$, $I_D=275\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.7 1.9	1.9 2.23	m Ω	$V_{GS}=10\text{ V}$, $I_D=100\text{ A}$ $V_{GS}=8\text{ V}$, $I_D=50\text{ A}$
Gate resistance	R_G	0.55	1.09	1.64	Ω	-
Transconductance	g_{fs}	100	200	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=100\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	8100	11000	pF	$V_{GS}=0\text{ V}$, $V_{DS}=60\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	2400	3100	pF	$V_{GS}=0\text{ V}$, $V_{DS}=60\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	40	70	pF	$V_{GS}=0\text{ V}$, $V_{DS}=60\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	21	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	19	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	38	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	19	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge ¹⁾	Q_{gs}	-	40	52	nC	$V_{DD}=60\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold ¹⁾	$Q_{g(th)}$	-	25	31	nC	$V_{DD}=60\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	24	36	nC	$V_{DD}=60\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	42	-	nC	$V_{DD}=60\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	113	141	nC	$V_{DD}=60\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.9	-	V	$V_{DD}=60\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	267	334	nC	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test.

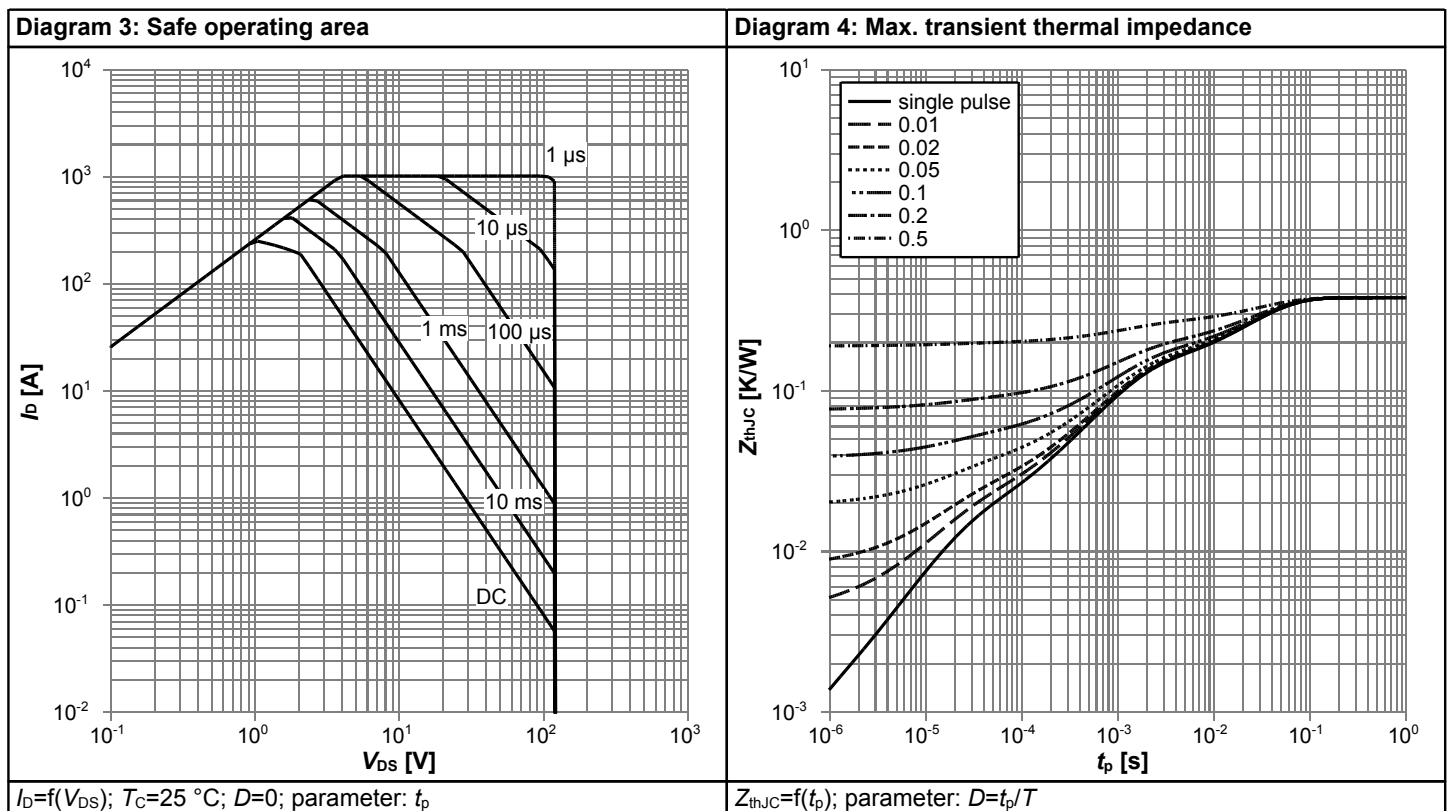
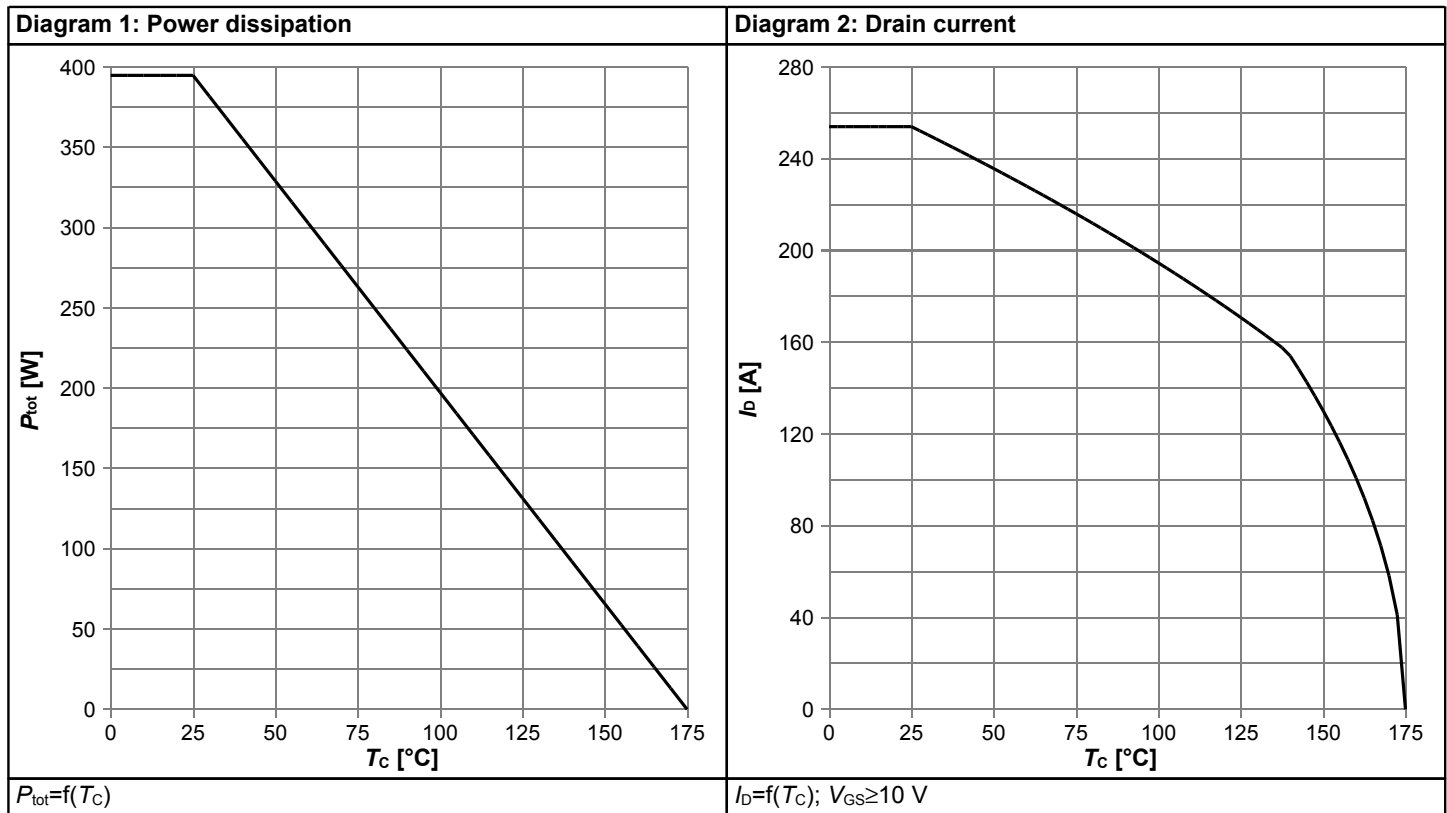
²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	223	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	1016	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.85	1.0	V	$V_{GS}=0\text{ V}$, $I_F=100\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	43	86	ns	$V_R=60\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=300\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	125	250	nC	$V_R=60\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=300\text{ A}/\mu\text{s}$
Reverse recovery time ¹⁾	t_{rr}	-	35	70	ns	$V_R=60\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	336	672	nC	$V_R=60\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$

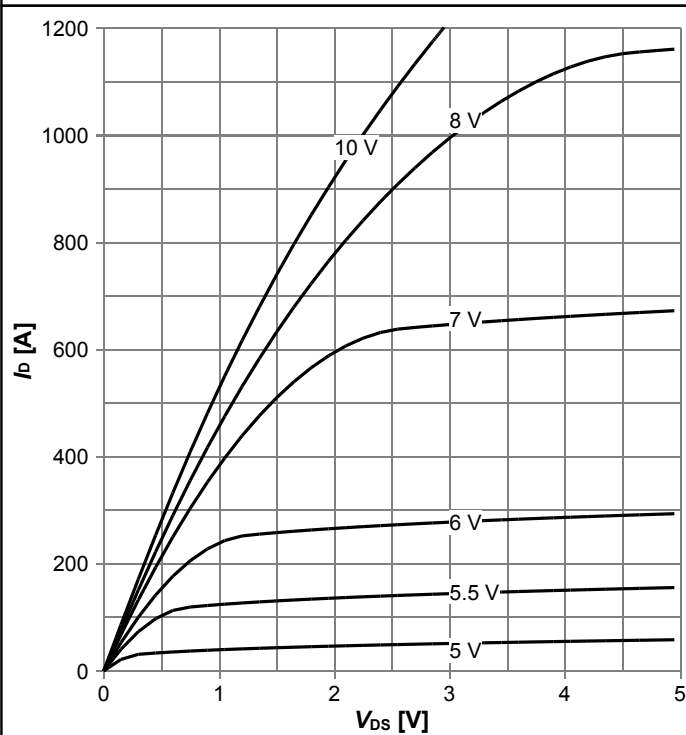
¹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams



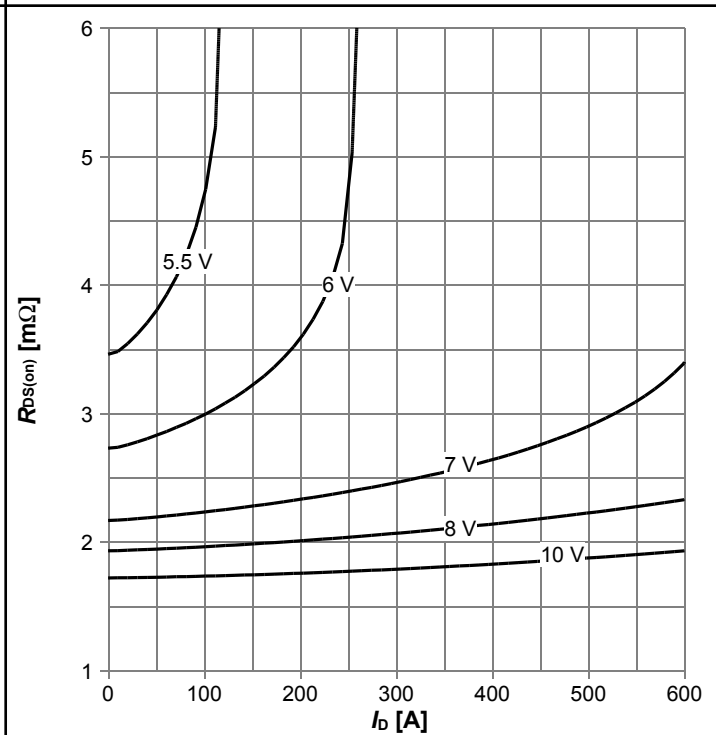
OptiMOS™ 6 Power-Transistor, 120 V
IPF019N12NM6

Diagram 5: Typ. output characteristics



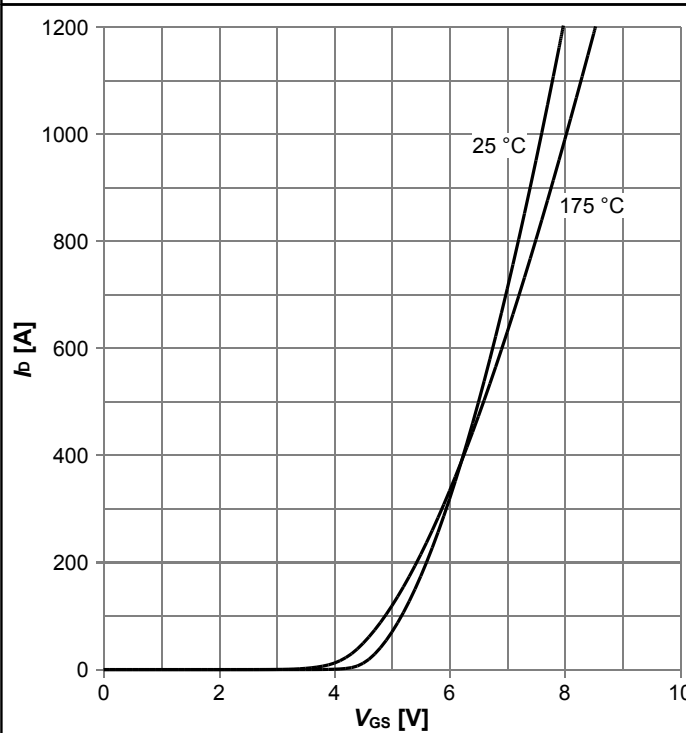
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



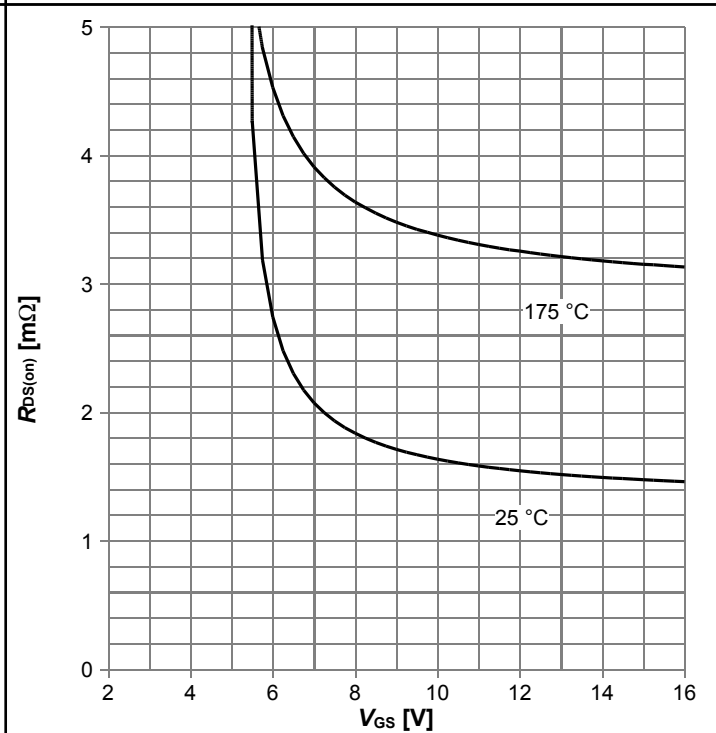
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



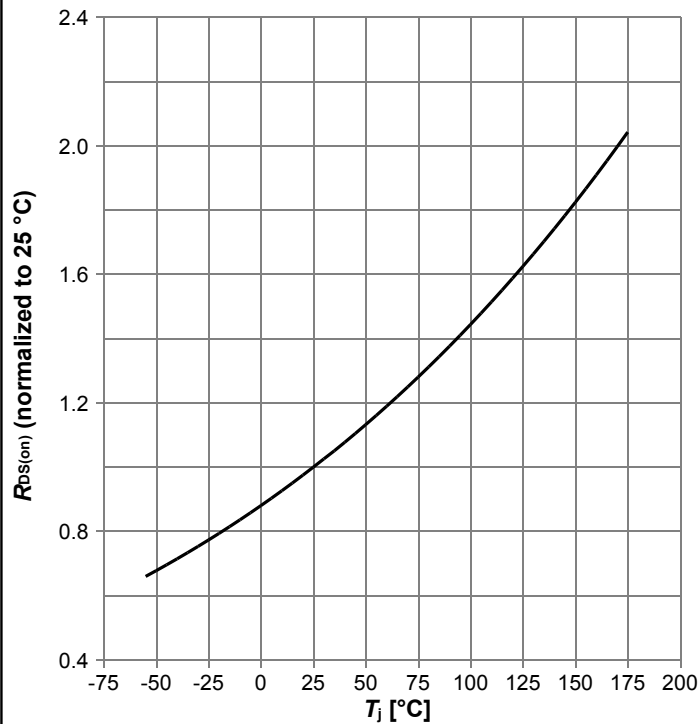
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



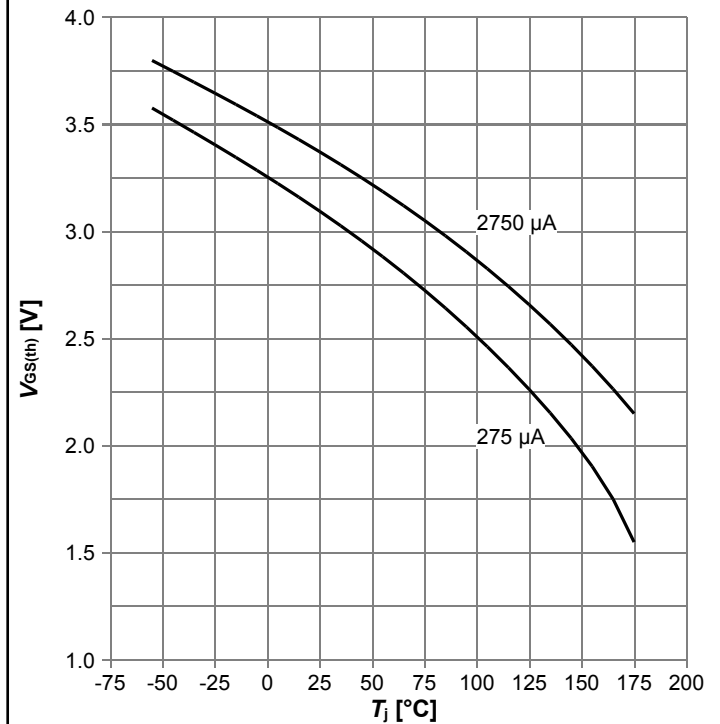
$R_{DS(on)} = f(V_{GS})$, $I_D = 100\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



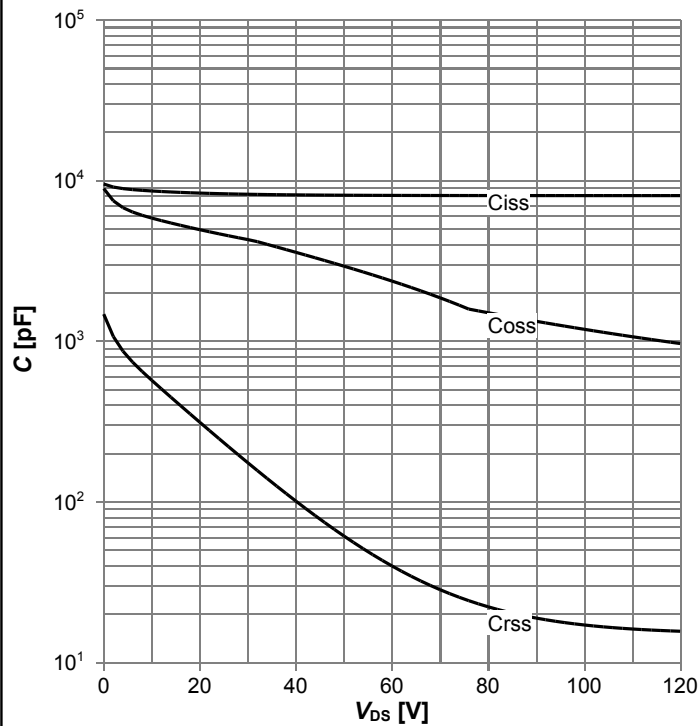
$R_{DS(on)} = f(T_j)$, $I_D = 100$ A, $V_{GS} = 10$ V

Diagram 10: Typ. gate threshold voltage



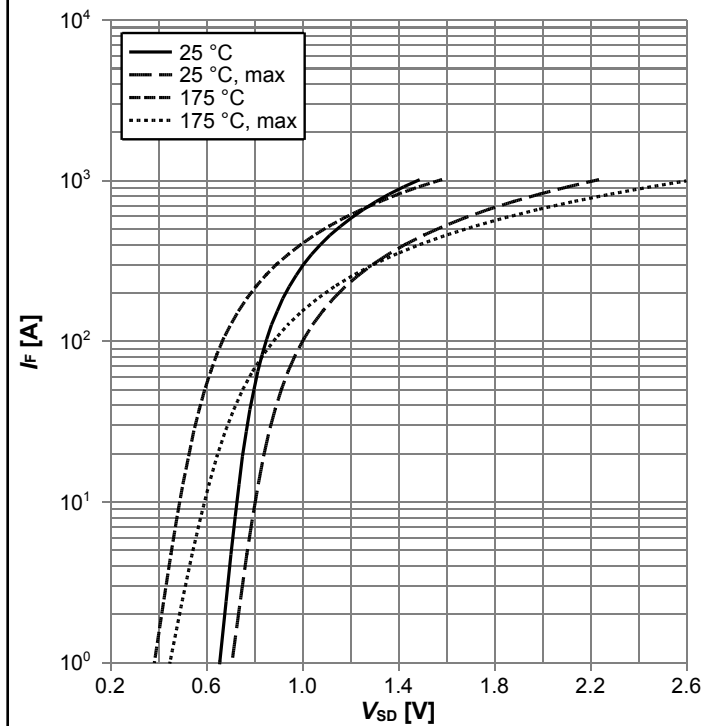
$V_{GS(th)} = f(T_j)$, $V_{GS} = V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



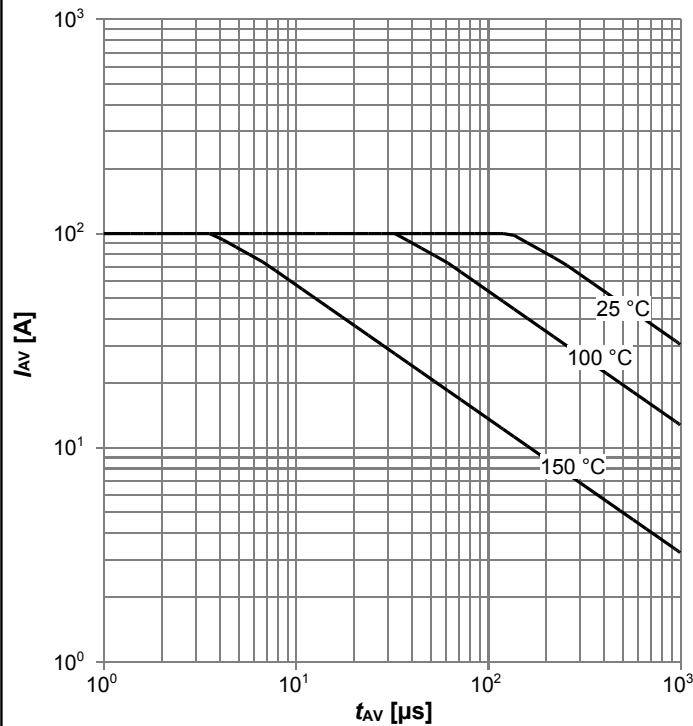
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz

Diagram 12: Forward characteristics of reverse diode



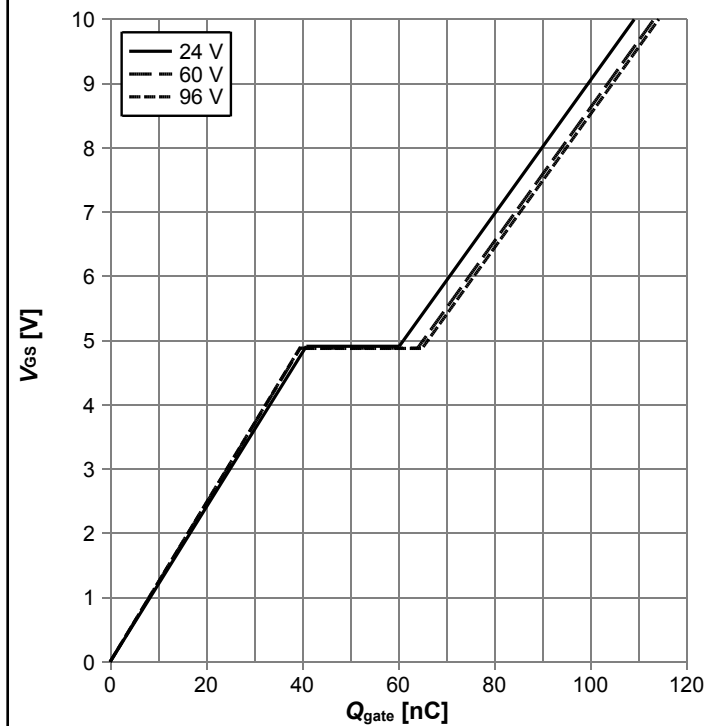
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



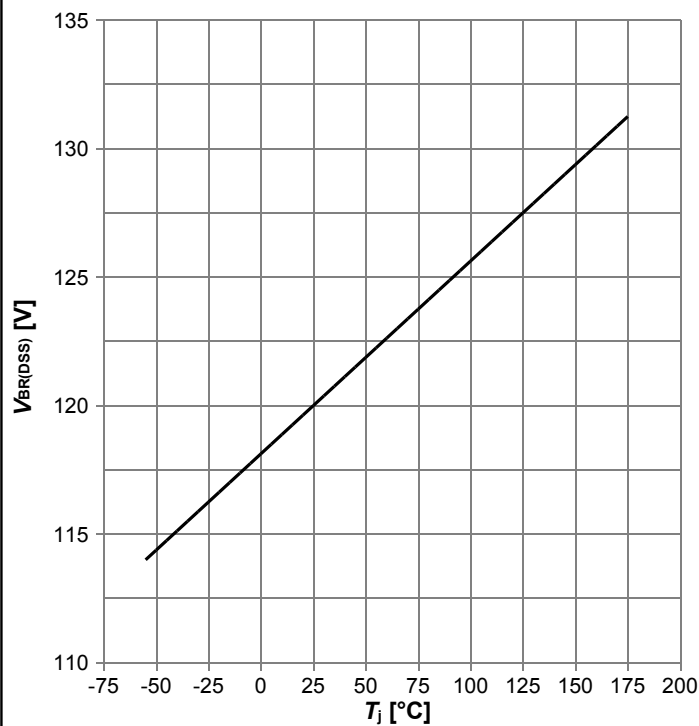
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate})$, $I_D=50\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

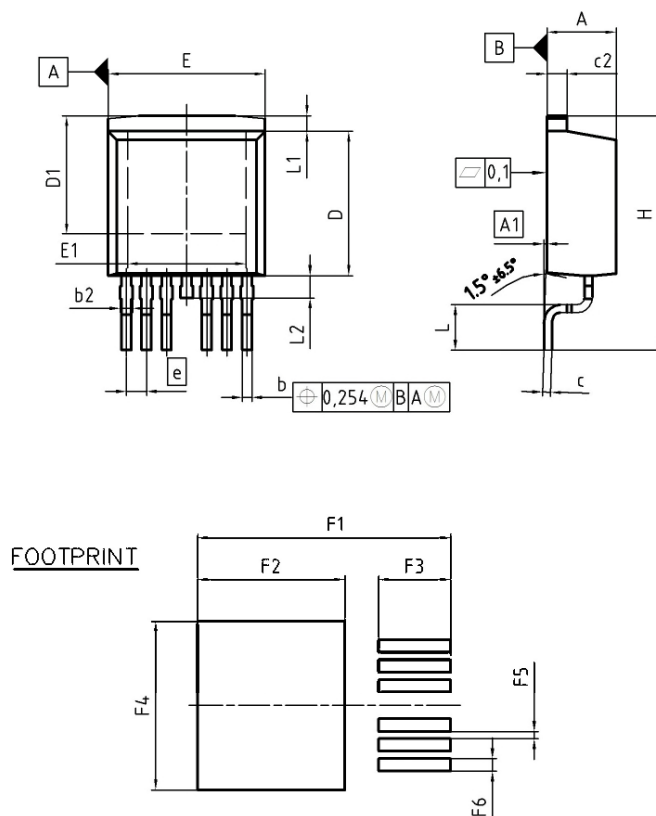


$V_{BR(DSS)}=f(T_j)$; $I_D=1\text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.50	0.70	0.020	0.028
b2	0.50	1.00	0.020	0.039
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	6.90	7.90	0.272	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	1.27		0.050	
N	6		6	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	0.37	0.57	0.015	0.022
F6	0.70	0.90	0.028	0.035

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EUROPEAN PROJECTION
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REVISION 01

Figure 1 Outline PG-TO263-7, dimensions in mm/inches

Revision History

IPF019N12NM6

Revision: 2023-02-03, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2023-02-03	Release of final version

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